High Power Laser Diode TO-Cans

Part Number: TO9-174

High Power TO9 Package Single-Mode Fabry-Perot Pulsed Wavelength at 1650nm Lensed Options Available

Features

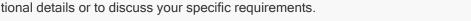
- **High Output Power**
- High Dynamic Range •
- High Efficiency
- Standard TO9
- **Cost Effective**

Application

- **Telecom OTDR**
- Laser Range Finder
- Target Illumination •



SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary, we will further optimize the design of our InP & GaSb laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.









Specification

TO9-174



Optical	Symbol	Тур.	Units
Center Wavelength	λ _c	1650	nm (±20)
Output Power (<10ns)*	Pout	1.4	Watts (±10%)
Output Power (150ns)*	Pout	0.5	Watts (±10%)
Emitter Width	W	5	μm
Spectral Width FWHM	Δλ	10	nm
Slope Efficiency	η	0.35	W/A
Fast Axis Div.	Θ⊥	28	deg FWHM
Slow Axis Div.	Θ _{II}	10	deg FWHM
Electrical	Symbol		Units
Power Conversion Eff.	η	10	%
Operating Current (<10ns)	lop	4	А
Operating Current (150ns)	l _{op}	2	А
Threshold Current	Ітн	0.05	А
Operating Voltage	V _{op}	3.2	V
Duty Cycle	DC	0.1	%
Mechanical	Symbol	Range	Units
Operating Temp.**		-40 to 60	°C
Storage Temp.		-40 to 80	°C

*Specified values are rated at a constant heat sink temperature of 20°C. **High temperature operation will reduce performance and MTTF. Unless otherwise indicated all values are nominal.

*Available Lenses & Caps

Part Number	Description	
TO9-174	TO9 Uncapped	
TO9-174-114	TO9 Cap, 4.6mm Tall	
TO9-174-115	TO9 5.8mm Tall Cap, Lens Collimated<5mrad f=590um,5mm lg	
TO9-174-140	TO9 5.8mm Tall Cap, Lens Matched f=171um, 5.0 lg	
TO9-174-161	TO9 Cap 5.8mm Tall	

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SemiNex Laser Diodes TO9-174

Graphs & Data

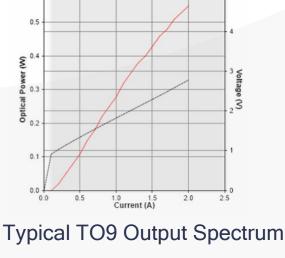
0.6 LIV Plot

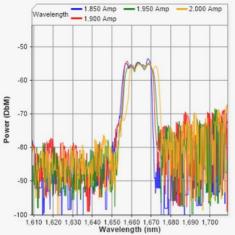
Typical TO9 L-I-V Characteristics

Optical Power (W) Voltage (V)

0.1 0.0 2.5 0.0 0.5 1.0 1.5 Current (A) 2.0

*Tested with 150nsec pulse @ 0.1% Duty Cycle







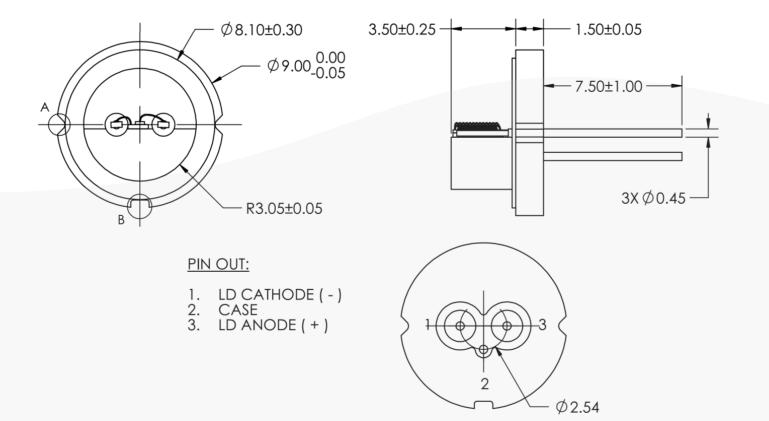


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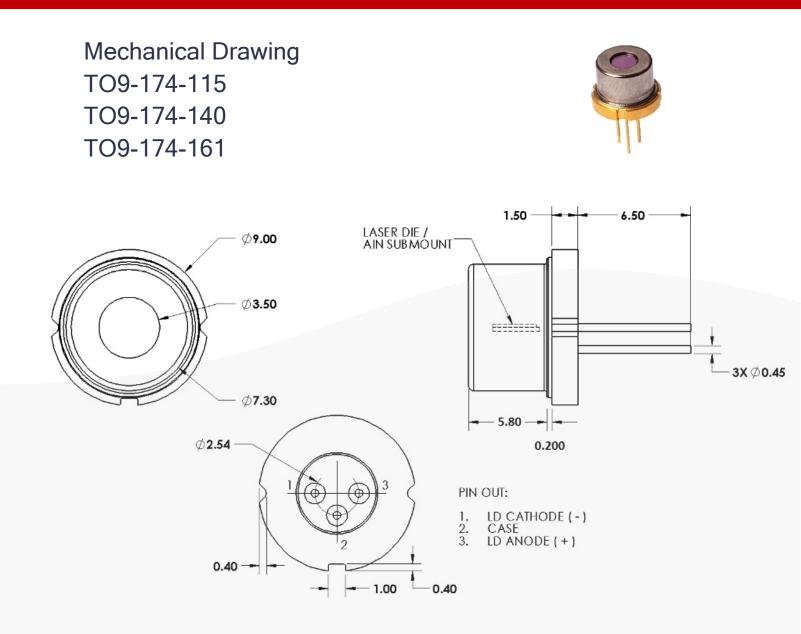
Mechanical Drawing TO9-174





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High Power Laser Diode

TO-Cans

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DANGER

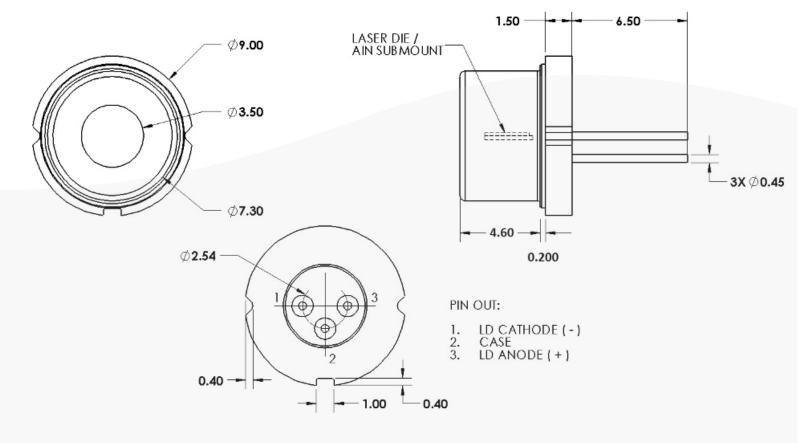
NVISIBLE LASER RAD RECT EXPOSURE TO

CLASS IIIb and IV LASER

PRODUCTS







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